

DATA SHEET

For a complete data sheet, please also download:

- The IC04 LOC莫斯 HE4000B Logic Family Specifications HEF, HEC
- The IC04 LOC莫斯 HE4000B Logic Package Outlines/Information HEF, HEC

HEF4016B **gates** **Quadruple bilateral switches**

Product specification
File under Integrated Circuits, IC04

January 1995

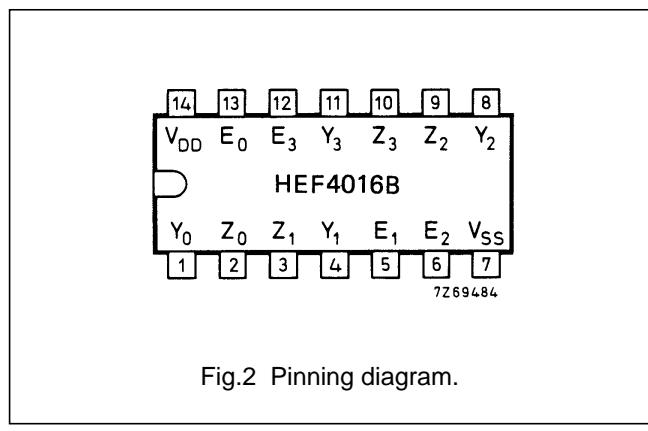
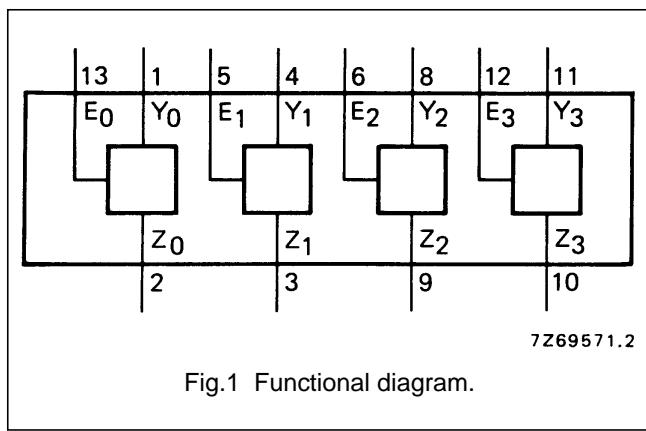
Quadruple bilateral switches

**HEF4016B
gates**

DESCRIPTION

The HEF4016B has four independent analogue switches (transmission gates). Each switch has two input/output terminals (Y/Z) and an active HIGH enable input (E). When E is connected to V_{DD} a low impedance bidirectional path between Y and Z is established (ON condition). When E is connected to V_{SS} the switch is disabled and a high

impedance between Y and Z is established (OFF condition). Current through a switch will not cause additional V_{DD} current provided the voltage at the terminals of the switch is maintained within the supply voltage range; V_{DD} ≥ (V_Y, V_Z) ≥ V_{SS}. Inputs Y and Z are electrically equivalent terminals.



PINNING

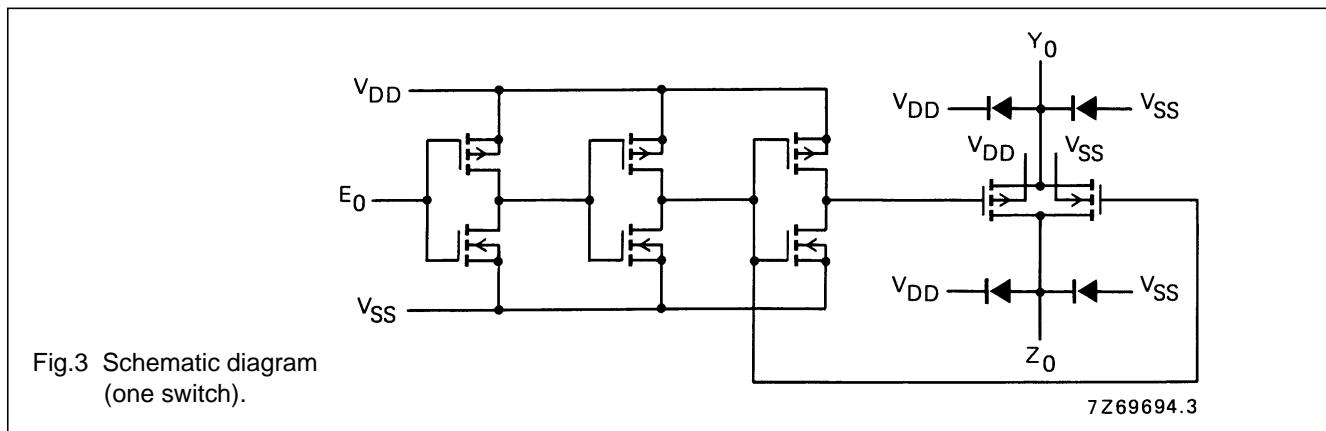
E ₀ to E ₃	enable inputs
Y ₀ to Y ₃	input/output terminals
Z ₀ to Z ₃	input/output terminals

HEF4016BP(N): 14-lead DIL; plastic (SOT27-1)
HEF4016BD(F): 14-lead DIL; ceramic (cerdip) (SOT73)
HEF4016BT(D): 14-lead SO; plastic (SOT108-1)
(): Package Designator North America

APPLICATION INFORMATION

Some examples of applications for the HEF4016B are:

- Signal gating
- Modulation
- Demodulation
- Chopper



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Limiting values in accordance with the Absolute Maximum System (IEC 134)

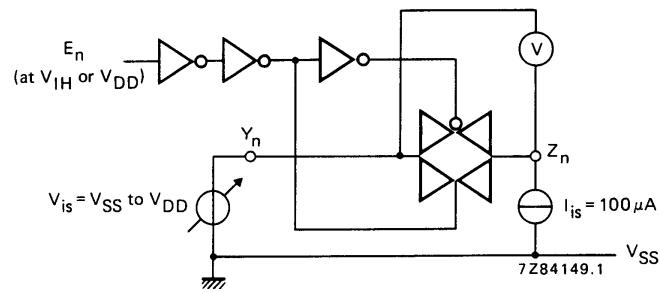
Power dissipation per switch	P	max.	100	mW
For other RATINGS see Family Specifications				

DC CHARACTERISTICS $T_{amb} = 25^\circ\text{C}$; $V_{SS} = 0\text{ V}$ (unless otherwise specified)

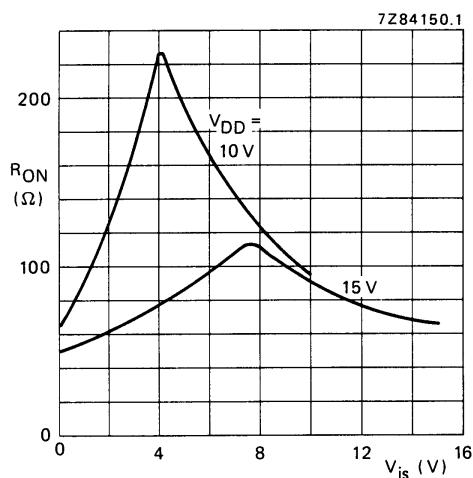
PARAMETER	V_{DD} V	SYMBOL	TYP.	MAX.	UNIT	CONDITIONS
ON resistance	5	R_{ON}	8000	—	Ω	E_n at V_{IH} ; $V_{is} = 0$ to V_{DD} ; see Fig.4
	10		230	690	Ω	
	15		115	350	Ω	
ON resistance	5	R_{ON}	140	425	Ω	E_n at V_{IH} ; $V_{is} = V_{SS}$; see Fig.4
	10		65	195	Ω	
	15		50	145	Ω	
ON resistance	5	R_{ON}	170	515	Ω	E_n at V_{IH} ; $V_{is} = V_{DD}$; see Fig.4
	10		95	285	Ω	
	15		75	220	Ω	
'Δ' ON resistance between any two channels	5	ΔR_{ON}	200	—	Ω	E_n at V_{IH} ; $V_{is} = 0$ to V_{DD} ; see Fig.4
	10		15	—	Ω	
	15		10	—	Ω	

PARAMETER	V_{DD} V	SYMBOL	T_{amb} ($^\circ\text{C}$)						UNIT	CONDITION
			-40	+25	+85	MIN.	MAX.	MIN.		
Quiescent device current	5	I_{DD}	—	1,0	—	1,0	—	7,5	μA	$V_{SS} = 0$; all valid input combinations; $V_I = V_{SS}$ or V_{DD}
	10		—	2,0	—	2,0	—	15,0	μA	
	15		—	4,0	—	4,0	—	30,0	μA	
Input leakage current at E_n	15	$\pm I_{IN}$	—	—	—	300	—	1000	nA	E_n at V_{SS} or V_{DD}
OFF-state leakage current, any channel OFF	5	I_{OZ}	—	—	—	—	—	—	nA	E_n at V_{IL} ; $V_{is} = V_{SS}$ or V_{DD} ; $V_{os} = V_{DD}$ or V_{SS}
	10		—	—	—	—	—	—	nA	
	15		—	—	—	200	—	—	nA	
E_n input voltage LOW	5	V_{IL}	—	1,5	—	1,5	—	1,5	V	switch OFF; see Fig.9 for I_{OZ}
	10		—	3,0	—	3,0	—	3,0	V	
	15		—	4,0	—	4,0	—	4,0	V	
E_n input voltage HIGH	5	V_{IH}	3,5	—	3,5	—	3,5	—	V	low-impedance between Y and Z (ON condition) see R_{ON} switch
	10		7,0	—	7,0	—	7,0	—	V	
	15		11,0	—	11,0	—	11,0	—	V	

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$E_n > V_{IH}$
 $I_{is} = 100 \mu A$
 $V_{SS} = 0 V$

Fig.5 Typical R_{ON} as a function of input voltage.

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AC CHARACTERISTICS

 $V_{SS} = 0 \text{ V}$; $T_{amb} = 25^\circ\text{C}$; input transition times $\leq 20 \text{ ns}$

	V_{DD} V	SYMBOL	TYP.	MAX.	
Propagation delays $V_{IS} \rightarrow V_{OS}$ HIGH to LOW	5 10 15	t_{PHL}	25 10 5	50 20 10	ns ns ns
					note 1
LOW to HIGH	5 10 15	t_{PLH}	20 10 5	40 20 10	ns ns ns
					note 1
Output disable times $E_n \rightarrow V_{OS}$ HIGH	5 10 15	t_{PHZ}	90 80 75	130 110 100	ns ns ns
					note 2
LOW	5 10 15	t_{PLZ}	85 75 75	120 100 100	ns ns ns
					note 2
Output enable times $E_n \rightarrow V_{OS}$ HIGH	5 10 15	t_{PZH}	40 20 15	80 40 30	ns ns ns
					note 2
LOW	5 10 15	t_{PZL}	40 20 15	80 40 30	ns ns ns
					note 2
Distortion, sine-wave response	5 10 15		— 0,08 0,04	% % %	
					note 3
Crosstalk between any two channels	5 10 15		— 1 —	MHz MHz MHz	
					note 4
Crosstalk; enable input to output	5 10 15		— 50 —	mV mV mV	
					note 5
OFF-state feed-through	5 10 15		— 1 —	MHz MHz MHz	
					note 6
ON-state frequency response	5 10 15		— 90 —	MHz MHz MHz	
					note 7

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V_{IS} is the input voltage at a Y or Z terminal, whichever is assigned as input.

V_{OS} is the output voltage at a Y or Z terminal, whichever is assigned as output.

1. $R_L = 10 \text{ k}\Omega$ to V_{SS} ; $C_L = 50 \text{ pF}$ to V_{SS} ; $E_n = V_{DD}$; $V_{IS} = V_{DD}$ (square-wave); see Figs 6 and 10.
2. $R_L = 10 \text{ k}\Omega$; $C_L = 50 \text{ pF}$ to V_{SS} ; $E_n = V_{DD}$ (square-wave);
 $V_{IS} = V_{DD}$ and R_L to V_{SS} for t_{PHZ} and t_{PZH} ;
 $V_{IS} = V_{SS}$ and R_L to V_{DD} for t_{PLZ} and t_{PZL} ; see Figs 6 and 11.
3. $R_L = 10 \text{ k}\Omega$; $C_L = 15 \text{ pF}$; $E_n = V_{DD}$; $V_{IS} = \frac{1}{2}V_{DD(p-p)}$ (sine-wave, symmetrical about $\frac{1}{2}V_{DD}$);
 $f_{IS} = 1 \text{ kHz}$; see Fig. 7.
4. $R_L = 1 \text{ k}\Omega$; $V_{IS} = \frac{1}{2}V_{DD(p-p)}$ (sine-wave, symmetrical about $\frac{1}{2}V_{DD}$);

$$20 \log \frac{V_{OS}(B)}{V_{IS}(A)} = -50 \text{ dB}; E_n(A) = V_{SS}; E_n(B) = V_{DD}; \text{see Fig. 8.}$$

5. $R_L = 10 \text{ k}\Omega$ to V_{SS} ; $C_L = 15 \text{ pF}$ to V_{SS} ; $E_n = V_{DD}$ (square-wave); crosstalk is $|V_{OS}|$ (peak value);
see Fig. 6.
6. $R_L = 1 \text{ k}\Omega$; $C_L = 5 \text{ pF}$; $E_n = V_{SS}$; $V_{IS} = \frac{1}{2}V_{DD(p-p)}$ (sine-wave, symmetrical about $\frac{1}{2}V_{DD}$);

$$20 \log \frac{V_{OS}}{V_{IS}} = -50 \text{ dB}; \text{see Fig. 7.}$$

7. $R_L = 1 \text{ k}\Omega$; $C_L = 5 \text{ pF}$; $E_n = V_{DD}$; $V_{IS} = \frac{1}{2}V_{DD(p-p)}$ (sine-wave, symmetrical about $\frac{1}{2}V_{DD}$);

$$20 \log \frac{V_{OS}}{V_{IS}} = -3 \text{ dB}; \text{see Fig. 7.}$$

	$\frac{V_{DD}}{V}$	TYPICAL FORMULA FOR P (μW)	
Dynamic power dissipation per package (P) ⁽¹⁾	5 10 15	$550 f_i + \sum (f_o C_L) \times V_{DD}^2$ $2600 f_i + \sum (f_o C_L) \times V_{DD}^2$ $6500 f_i + \sum (f_o C_L) \times V_{DD}^2$	where f_i = input freq. (MHz) f_o = output freq. (MHz) C_L = load capacitance (pF) $\sum (f_o C_L)$ = sum of outputs V_{DD} = supply voltage (V)

Note

1. All enable inputs switching.

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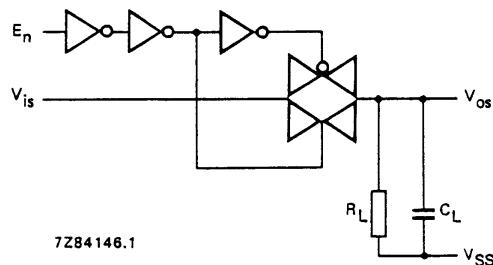
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Fig.6

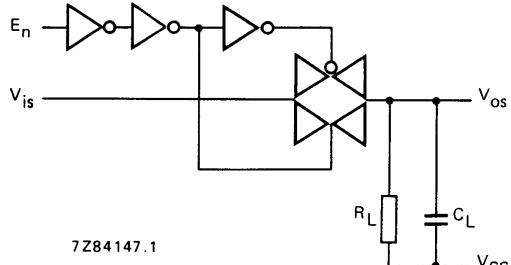
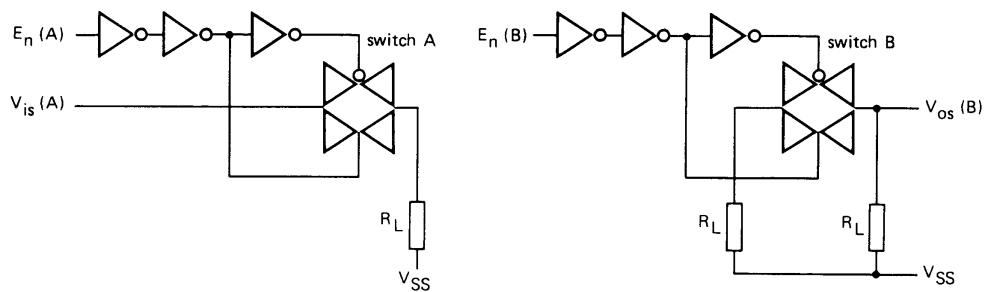


Fig.7



(a)

(b)

Fig.8

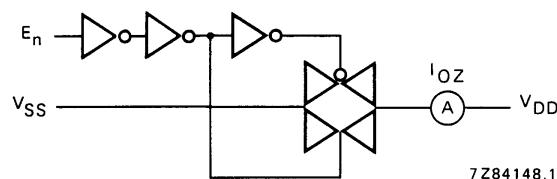
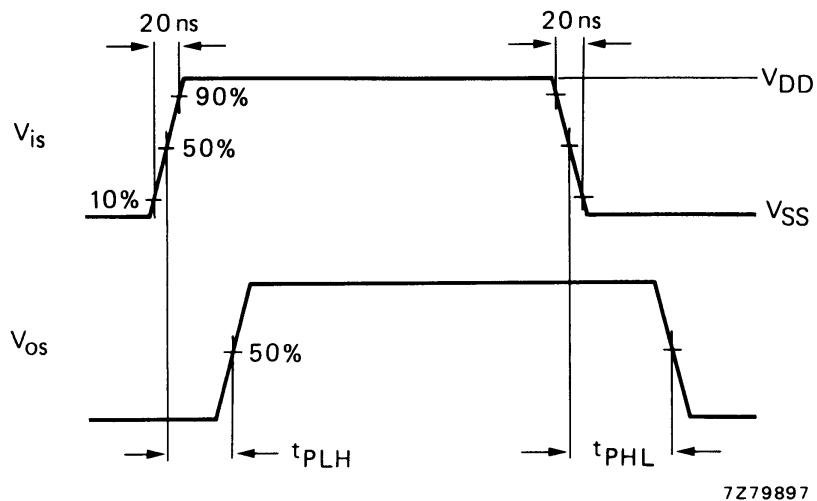
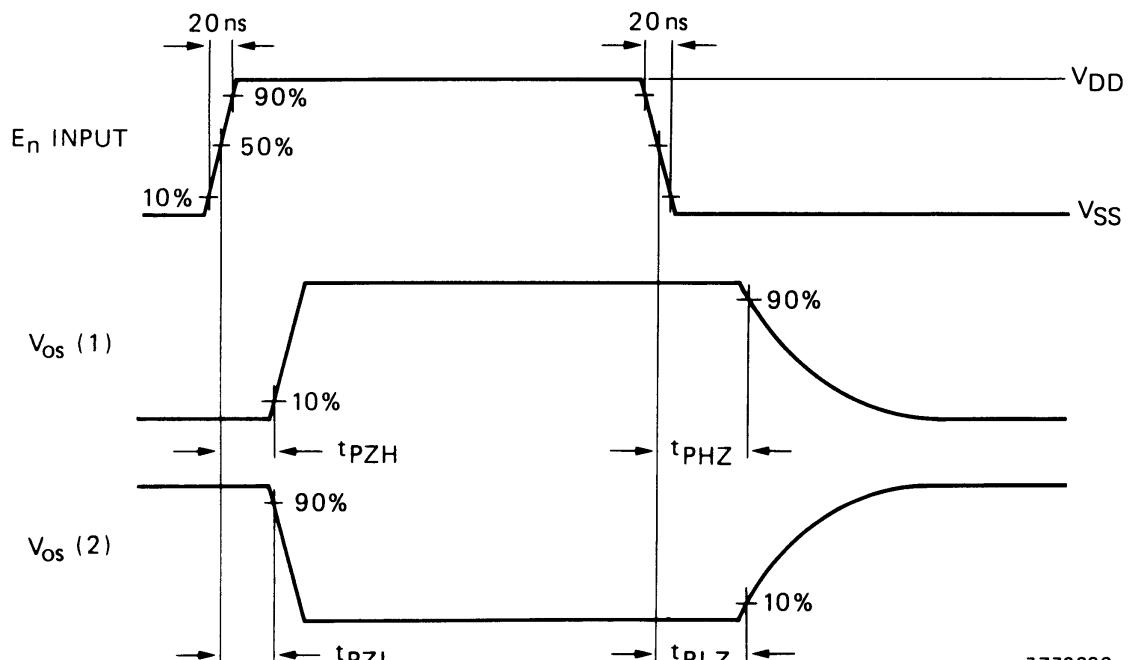


Fig.9

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- (1) V_{is} at V_{DD}
- (2) V_{is} at V_{SS}

Fig.11 Waveforms showing output disable and enable times.